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T-252 P01/06 U-614

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10/12/04	10/632,186	M-15241US	2813	\$180.00

Attached is the pertinent information regarding the charge for \$180.00 for the information disclosure statement under 37 C.F.R 1.17(p).

If any questions may arise please contact me through email at [adimayuga@macpherson-kwok.com](mailto:adimayuga@macpherson-kwok.com) or telephone me at 408-392-9250 ext. 246.

Thank you,  
Aviane Dimayuga

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MAR 02 2006

Application No.: 10/632,186 Filing Date: July 30, 2003

Confirmation No.: 3961

First Named Inventor: Yi Ding

Assignee: ProMOS Technologies, Inc.

Examiner: Nguyen, Thanh T. Art Unit: 2813

Attorney Docket No.: M-15241 US

San Jose, California  
October 12, 2004Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(C)

Dear Sir:

Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed except for United States Patent and United States Published Patent Applications.

Citation of these documents shall not be construed as:

1. an admission that the documents are necessarily prior art with respect to the instant invention;

2. a representation that a search has been made, other than as described above;

or

3. an admission that the information cited herein is, or is considered to be material to patentability as defined in § 1.56(b).

03/03/2006 TL0111 00000026 502257 10632186

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Application No. 10/632,186

Please charge the fee of \$180.00 as set forth in 37 CFR 1.17(p) to deposit account 50-2257. Please charge any amount underpaid, or credit the amounts overpaid, to the same deposit account. This paper is being submitted in duplicate.

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Respectfully submitted,

*Michael Shenker*

Michael Shenker

Patent Attorney

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Application No. 10/632,186

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T-252 P04/06 U-614

Sheet 1 of 1

U.S. Department of Commerce, Patent and Trademark Office				Any Docket No.		Serial No.	
				M-15241 US		10/632,186	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant(s)			
(Use several sheets if necessary)				Yi Ding			
				Filing Date		Group	
				July 30, 2003		2813	
U.S. Patent Documents							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	6,265,739	Jul. 2001	Yaegashi et al.			
	AB	6,747,310	Jun. 2004	Fan et al.			
	AC	2003/0205776	Nov. 2003	Yaegashi et al.			
	AD	6,468,865	Oct. 2002	Yang et al.			
	AE	6,218,689	Apr. 2001	Chang et al.			
	AF	6,214,669	Apr. 2001	Hisamune			
	AG	6,162,682	Dec. 2000	Kleine			
	AH	6,232,185	May-01	Wang			
	AI	5,912,843	Jun. 1999	Jeng			
	AJ	6,436,764	Aug. 2002	Hsieh			
	AK	6,344,993	5 Feb. 2002	Harari et al.			
	AL	5,668,757	Sept. 1997	Jeng			
	AM	6,355,524	Mar. 2002	Tuan et al.			
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
Examiner		Date Considered					
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.</p>							

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U.S. Department of Commerce, Patent and Trademark Office		Atty Docket No.	Serial No.
		M-15241 US	Unassigned
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant(s)	
(Use additional sheets if necessary)		Yi Ding	
		Filing Date	Group
		Filed Herewith	Unassigned
U.S. Patent Documents			
*Examiner Initial	Number	Date	Name
AA	5,402,771	28 Mar. 1995	Owo
AB	5,856,943	6 Feb. 1999	Jenq
AC	6,057,575	2 May 2000	Jenq
AD	6,110,129	10 Oct. 2000	Chen
AE	6,134,144	17 Oct. 2000	Lin et al.
AF	6,171,999	9 Jan. 2001	Ding et al.
AG	6,190,006	11 Mar. 2001	Chen
AH	6,261,991	17 Jul. 2001	Chang et al.
AI	6,326,661	1 Oct. 2001	Dormans et al.
AT	6,355,004	12 Mar. 2002	Tuan et al.
AY	6,365,487	2 Apr. 2002	Choi
Citations (including Author, Title, Date, Pertinent Pages, Etc.)			
AI	Sakata, Rikihito "A Review of 256Mbit NAND Flash Memories and NAND Flash Future Trend," February 1999, Nonvolatile Memory Workshop in Monterey, California, pages 22-31.		
AM	Matsuda, Y.; Yamada, S.; Ohji, E.; Taguchi, S.; and Wada, M. "A New Flash-Erase EEPROM Cell with A Sidewall Select-Gate on the Source Side," 1989 IEEE, pages 604-606.		
AN	Wu, A.; Chen T.; Ho, P.K.; and Hu, C. "A Novel High-Speed, 5-Volt Programming EPROM Structure With Source Side Injection," 1986 IEEE, 584-587.		
AO	Mizutani, Yoshihiro and Makita, Koji "A New EPROM Cell With A Sidewall Floating Gate For High-Speed and High-Performance Device," 1985 IEEE, 635-638.		
AP	Chang, C.F.; Tsao, S.C.; Yamauchi, Y.; Yoshimi, M. "A Novel High-Speed Access Selectors for Memory Array Using Split-Gate Source-Side-Injection Cell for 5V-Only Accessing," 1994, Symposium on VLSI Technology Digest of Technical Papers, pages 49-50.		
AQ	Miyazaki, T.; et al. "A Novel Modular Triple Self-Aligned Embedded Split-Gate Flash Memory," 2000 Symposium on VLSI Technology Digest of Technical Papers, pages 120-121.		
AR	Ma, M.-H. et al., "A Novel 0.25 $\mu$ m Split-Gate EEPROM (DSG) Cell in Contactless Array for Single Vcc High Density Flash Memory," 1994 IEEE, 3.5.1-3.5.4.		
Examiner	Not Considered		
*EXAMINER: Initial if citation is not in conformance with MPEP 609; Draw line through citation if not in conformance with MPEP 609; Include copy of this form with your communication to applicant.			

Sheet 1 of 1

U.S. Department of Commerce, Patent and Trademark Office		Atty Docket No.	Serial No.
		M-15241 US	10/632,186
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant(s)	
(Use several sheets if necessary)		Yi Ding	
		Filing Date	Group
		July 30, 2003	Unassigned
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)			
		United States Patent Application No. 10/440,466, entitled "Fabrication Of Conductive Gates For Nonvolatile Memories From Layers With Protruding Portions," Filed on May 16, 2003; Attorney Docket No.: M-12979 US.	
	AB	United States Patent Application No. 10/440,005, entitled "Fabrication of Dielectric On A Gate Surface To Insulate The Gate From Another Element Of An Integrated Circuit," Filed on May 16, 2003; Attorney Docket No.: M-15203 US.	
	AC	United States Patent Application No. 10/440,508, entitled "Fabrication Of Gate Dielectric In Nonvolatile Memories Having Select, Floating And Control Gates," Filed on May 16, 2003; Attorney Docket No.: M-15204 US.	
	AD	United States Patent Application No. 10/440,500, entitled "Integrated Circuits With Openings that Allow Electrical Contact To Conductive Features Having Self-Aligned Edges," Filed on May 16, 2003; Attorney Docket No.: M-15201 US.	
	AE	United States Patent Application No. 10/393,212, entitled "Nonvolatile Memories And Methods Of Fabrication," Filed on March 19, 2003; Attorney Docket No.: M-12902 US.	
	AF	United States Patent Application No. 10/411,813, entitled "Nonvolatile Memories With A Floating Gate Having An Upward Protrusion," Filed on April 10, 2003; Attorney Docket No.: M-12903 US.	
	AG	United States Patent Application No. 10/393,202, entitled "Fabrication of Integrated Circuit Elements In Structures With Protruding Features," Filed on March 19, 2003; Attorney Docket No.: M-15151 US.	
	AH	United States Patent Application No. 10/631,941, entitled "Nonvolatile Memory Cell With Multiple Floating Gates Formed Over The Select Gate," Filed on July 30, 2003; Attorney Docket No.: M-15171 US.	
	AI	United States Patent Application No. 10/632,155, entitled "Nonvolatile Memory Cells With Buried Channel Transistors," Filed on July 30, 2003; Attorney Docket No.: M-15222 US.	
	AJ	United States Patent Application No. 10/632,007, entitled "Arrays Of Nonvolatile Memory Cells Wherein Each Cell Has Two Conductive Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15223 US.	
	AK	United States Patent Application No. 10/631,452, entitled "Fabrication Of Dielectric For A Nonvolatile Memory Cell Having Multiple Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15229 US.	
	AL	United States Patent Application No. 10/632,154, entitled "Fabrication Of Gate Dielectric In Nonvolatile Memories In Which A Memory Cell Has Multiple Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15221 US.	
	AM	United States Patent Application No. 10/631,552, entitled "Nonvolatile Memories And Methods Of Fabrication," Filed on July 30, 2003; Attorney Docket No.: M-12902-1P US.	
	AN		
Examiner		Not Considered	
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